Surface and horing on liquid crystalline polymerbrushes

Harald Lange^{y;z} and Friederike Schmid^{y;}

y Fakultat fur Physik, Universitat Bielefeld, 33615 Bielefeld, Germ any Telephone: + + 49-521-1066191, E-m ail: schmid@physik.uni-bielefeld.de z Institut fur Physik, Universitat M ainz, 55099 M ainz, Germ any

A bstract

W e present a M onte C arb study of the surface anchoring of a nem atic uid on swollen layers of graffed liquid crystalline chain m olecules. The liquid crystalline particles are m odeled by soft repulsive ellipsoids, and the chains are m ade of the same particles. An appropriately m odi ed version of the con gurational bias M onte C arb algorithm is introduced, which rem oves and redistributes chain bonds rather than whole m onom ers. W ith this algorithm, a wide range of graffing densities could be studied.

The substrate is chosen such that it favors a planar orientation (parallel to the surface). Depending on the grafting density, we nd three anchoring regimes: planar, tilted, and perpendicular alignment. At low grafting densities, the alignment is mainly driven by the substrate. At high grafting densities, the substrate gradually loses its in uence and the alignment is determined by the structure of the interface between the brush and the pure solvent instead.

Keywords: liquid crystals, surface anchoring PACS: 61.30 Hn, 61.30 V x

1. Introduction

Liquid crystals have fascinated condensed m atter physicists, chem ists and m aterial scientists for m any decades [1,2] { rst, because they exhibit a large number of beautiful phases with intriguing symmetries and interesting material properties, and second, because of their technological use, particularly in the dom ain of display devices. One important aspect for technical applications is the so-called surface anchoring [3{5]: Surfaces orient nearby molecules, and these in turn orient the whole bulk of the liquid crystal. A lignment layers are key components of liquid crystal display devices [5]. In particular, one is interested in designing surfaces which orient liquid crystals in a well-de ned way in any desired direction.

Possible candidates are liquid crystalline polym erbrushes [6{10].H alperin and W illiam s [6] have suggested to create a situation where a substrate which favors planar anchoring (parallel to the surface) competes with a stretched main-chain liquidcrystalline brush which favorshom eotropic anchoring (perpendicular to the surface). They predicted that this con ict would result in tilted anchoring above a critical grafting density c. In their scenario, the transition between planar and tilted anchoring is continuous. Above the transition, the grafting density can be used to tune the anchoring angle.

Experim entally, dense liquid crystalline polym er brushes have been prepared [9], and their alignm ent properties have been studied [10]. So far, the conditions in the experim ents were such that the substrate and the brush favor the same type of alignm ent. How ever, a com petition as required by the scenario of H alperin and W illiam s can be introduced by a straightforw ard m odi cation of the substrate [10].

M otivated by that work, we have investigated the consequences of such a competition by M onte C arbo simulations of an idealized liquid crystal m odel. We have studied brushes of liquid crystalline polymers in a nem atic solvent on a substrate which favors planar anchoring. The relaxation times in such system s are very high. Therefore, we have im plan ented a new version of the con gurational bias M onte C arb algorithm [11{14]: C hains are broken up such that their m onom ers turn into solvent particles, and solvent particles are linked together to form new chains.W ith this algorithm, a wide range of grafting densities could be considered. We shall see that the resulting anchoring scenario turns out to be quite rich.

W e introduce the simulation model in the next section, and describe the algorithm in the third section. The results are presented and discussed in section 4.W e sum marize and conclude in the last section.

2. The Sim ulation M odel

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O ur system consists of soft ellipsoidal particles with elongation = $_{end-end}$ = $_{side-side}$ = 3. Two particles i and j with orientations u_i and u_j separated by the center-center vector r_{ij} interact via the purely repulsive pair potential

$$V_{ij} = \begin{cases} \circ & 4_{0} (X_{ij}^{12} X_{ij}^{6}) + 0 : X_{ij}^{6} > 1 = 2 \\ \vdots & 0 & \vdots \text{ otherwise} \end{cases}$$
(1)

where X_{ij} =
$$_0 = (r_{ij} \quad ij + _0)$$
 and
 $_{ij} = _0 \quad 1 \quad \frac{h}{2} \frac{(u_i \quad r_j + u_j \quad r_j)^2}{1 + u_i \quad u_j}$

+
$$\frac{(u_{i} \pm u_{j} \pm u_{j})^{2} = 1}{1 \quad u_{i} = 4}$$
 (2)

with = $\binom{2}{1} = \binom{2}{2} + 1$. The function _{ij} approximates the contact distance between the two ellipsoids in the direction $\hat{r}_{ij} = r_{ij} = r_{ij}$ [15].

Solvent and chain particles have the same nonbonded interactions. In addition, chain m onom ers are connected by anharm onic springs of length b with equilibrium length b_0 and a logarithm ic cuto at $b \quad b_0 j = b_s$. At $b \quad b_0 j < b_s$, the spring potential is given by

$$V_{s}$$
 (b) = $k_{s}=2b_{s}^{2}\ln[1 (b b_{0})^{2}=b_{s}^{2})]$: (3)

The direction of a bond is given by the unit vector $\hat{b} \cdot A$ sti ness potential

$$V_{a}$$
 ($u_{i}\hat{b}_{1}\hat{b}_{2}$) = k_{a} ($j_{1}\hat{b}_{1}j$ + $j_{1}\hat{b}_{2}j$ + $2\hat{b}_{1}\hat{b}_{2}$) (4)

is imposed, which penalizes non-zero angles between the orientation u of a monom er and its two adjacent bonds \hat{b}_1 and \hat{b}_2 . The system is conned by hard walls at two sides z = 0 and $z = L_z$: The distance between the walls and the centers of ellipsoids, which have an angle with respect to the surface normal, must exceed

$$d_{z}() = {}_{0}=2^{b} \frac{1}{1+\cos^{2}()(^{2} 1)};$$
 (5)

The chains are grafted to the walls at one end, the grafting points are arranged on a regular square lattice.

W e have studied system swith roughly N = 2000 solvent particles (the num bers varied in the di erent runs) and up to 242 chains of four m onom ers. The simulation boxes were rectangular of size L_k

 L_k L_z with periodic boundary conditions in the lateral directions and xed boundary conditions in the z direction. The thickness L_z was allowed to uctuate, so that the simulations could be performed at constant pressure. The lateral size $L_k =$ 12_0 waskept xed in order to maintain a constant grafting density .Trialm oves included monomer displacements, monomer rotations, rescaling of L_z , and the congurational bias moves described in the next section. The initial conguration was set up such that all particles pointed in the x direction. The system was then equilibrated over at least 1 m illion M onte C arb steps, and data were collected over 5 or more m illion M onte C arb steps. O ne M onte C arlo step" includes on average N attem pts ofm onom er displacem ents, 2N attem pts of m onom er rotations, one attem pt of L_z rescaling, and one attem pt of a con gurational bias m ove.

The model parameters chosen were $k_{\rm s}=k_{\rm a}=10$; $b_0=4$; and $b_{\rm s}=0.8$. Here and throughout, we use scaled units de ned in terms of $_0, _0$, and the Boltzm ann constant $k_{\rm B}$. Unless stated otherwise, the simulations were performed at constant temperature T=0.5 and constant pressure P=3. The average number density in the bulk was h i= 0:313.

3. C on gurationalBiasM onteCarlo in a Solvent

The most frequently used continuous space version of the con gurational bias M onte Carlo algorithm [12,16] removes chains from the system and inserts new monomers into the system . How ever, this method is not e ective in our system, because the space is densely lled with m onom er and solvent particles, and little free volume for new particles is available. Therefore, we have resorted to a dierent scheme. Instead of removing the monom ers of a chain, we only remove the connecting bonds and redistribute them such that new chains are form ed from solvent particles. This m ethod resembles closely the lattice version of the con gurational bias M onte Carlo algorithm [12]. The only di erence is that the lattice is now random, with \lattice sites" given by the centers of solvent orm onom er particles.

In practice, we proceed as follows: First, we remove all the bonds from a random ly chosen chain. Then we nd all n_1 solvent particles, which are at a distance b 2 $[b_0 \ b_s; b_0 + b_s]$ from the grafting point, and choose one of them according to the Boltzm ann probability

$$P_{1} = \frac{1}{Z_{1}} \exp^{h} \frac{V_{s}(b_{1}) + k_{a}(1 - ju_{1}\hat{b}_{1})}{T}^{1}$$
(6)

Here b_1 is the length of the bond between the grafting point and the particle, \hat{b}_1 its direction, and u_1 the orientation of the particle. The normalization factor Z_1 is the sum

$$Z_{1} = \exp_{j=1}^{X_{1}} \exp_{j=1}^{h} \frac{V_{s}(b_{1,j}) + k_{a}ju_{1,j}\hat{b}_{1,j}j}{T}^{1}$$
(7)

overthe Boltzm ann factors for all n_1 potential candidates j.W e continue in the same spirit and construct a new trial chain m onom er by m onom er: G iven the (1)th m onom er, we identify all n solvent particles at the distance b 2 $[b_0 \ b_s; b_0 + b_s]$ from the (1)th m onom er, and pick one with the probability

$$P = \frac{1}{Z} \exp \left(\frac{1}{T} \nabla_{s} \left(b \right) \right)$$

$$k_{a} (j \mu_{1} \hat{b} j + 2\hat{b}_{1} \hat{b} + j \mu \hat{b} j) \qquad (8)$$

with

$$Z = \sum_{j=1}^{X} \exp \frac{1}{T} V_{s} (b_{j})$$

$$k_{a} (j_{1} \ _{1}\hat{b}_{j} j + \hat{b} \ _{1}\hat{b}_{j} + j_{1} ;_{j}\hat{b}_{j} (j)$$
(9)

The total probability of constructing a given new chain with M monomers is

$$P_{new} = \begin{array}{c} \Psi \\ P \\ = 1 \end{array} P \quad : \tag{10}$$

For the nalM etropolis step, one also has to $com - pute the probability P_{old}$ that the original, initially rem oved chain is constructed. The way to do this is exactly analogous, except that the m onom ers are not picked random ly. The new chain is accepted with the probability

$$W_{old! new} = m in 1; \frac{P_{old}}{P_{new}} exp(E=T);$$
 (11)

where E is the energy di erence between the old and the new chain. Since no particles were m oved, E only contains contributions of the bond energies. If the m ove is not accepted, the original chain is restored.

A sim ilarm ethod has been described recently by W ijm ans et al [14]. The im plem entation of this algorithm was essential for the success of our sim ulations.W ith the new algorithm, the con gurations equilibrated w ithin a m illion M onte C arlo steps and reliable data for a range of grafting densities could be collected.

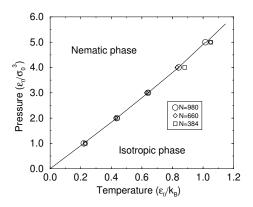


Fig.1. Bulk phase diagram in pressure-tem perature space, calculated from simulations with three di erent system sizes as indicated.

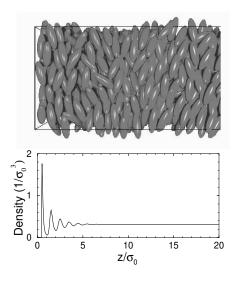


Fig. 2. Solvent in contact with the bare substrate; con guration snapshot (top) and number density pro le vs.z (bottom).

4. Results

Before investigating the full system, we have characterized the dierent constituents of our system separately.

The bulk phase diagram of the solvent particles was determ ined from simulations of cubic systems with periodic boundary conditions in all di-

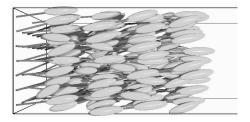


Fig. 3. C on guration snapshot of grafted chains without solvent at the grafting density = $0.34= \frac{2}{0}$.

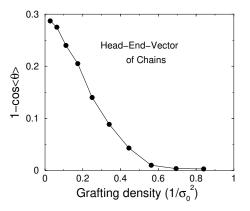


Fig. 4. G raffed chains without solvent: A verage tilt angle h i of the head-to-end vector of the chains as a function of the grafting density $\ .$

rections. The resulting phase diagram in P T space is shown in Figure 1. The state point of our later simulations at T = 0.5, P = 3 is well in the nem atic phase. The coexistence densities at P = 3 are $_{\text{Nem atic}}$ 0.29, and $_{\text{Isotropic}}$ 0.28. The system s were too small to allow for an accurate determ ination of the coexistence gap in T space. In P T space, how ever, the phase boundaries are not a ected much by nite size e ects (Figure 1).

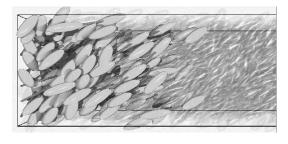
A bare substrate w ithout graffed chains orients the particles parallel to itself. A snapshot is shown in Figure 2. The density pro le reveals strong layering e ects in close vicinity to the wall, which decay rapidly in the bulk.

F inally, we have studied the behavior of brushes without solvent. A snapshot for a system with the moderate grafting density = $0.34 = \frac{2}{0}$ is show n

in Figure 3. The chains are disordered, with chain orientations distributed around = 0 (being the angle with respect to the substrate norm al). The average angle h i of the head-to-end vectors decreases rapidly with increasing grafting density (Figure 4).

W e turn to the discussion of the results for the full system . Figure 5 shows a snapshot of a brush with solvent at the grafting density $= 0.34 = \frac{2}{0}$. C om paring this gure with Figure 4, we note that the presence of the solvent makes the brush m uch m ore compact, i.e., the solvent particles introduce an e ective attractive interaction between the chains. The chains are tilted in a common direction (Figure 5 (top)). The tilt propagates into the bulk of the system outside of the brush (Figure 5 (bottom)). As anticipated in the introduction, we thus nd that a brush can induce tilt in the orientation of a nem atic solvent.

The comparison of Figure 4 and Figure 6 (top) shows that the average tilt angle h i of the head-



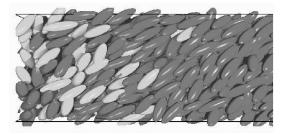


Fig. 5. C on guration snapshot of grafted chains with solvent at grafting density = $0.34 = \frac{2}{0}$. Top: Just chain m onom ers (solvent particles are transparent); B ottom : C hain m onom ers (light) and solvent particles (dark).

to-end vector of chains increases in the presence of the solvent at all grafting densities. M ost notably, the chains rem ained tilted up to the highest grafting densities that we considered. How ever, the tilt of the chains does not always produce tilted anchoring in the nem atic bulk uid. Figure 6 (bottom) dem onstrates that the solvent particles have less tilt than the chain particles, and stand alm ost perpendicular to the surface at the highest grafting density. In fact, a closer inspection of our data show s that the rem aining average angle h i stem s m ainly from the contribution of the solvent particles inside of the brush, and from orientational disorder of the particles outside of the brush. A m ore detailed discussion will be presented elsew here [17].

Figure 6 (bottom) reveals a second feature of the system : At low grafting densities, the wall aligns the solvent particles in a planar way, i. e., the alignm ent is basically determ ined by the anchoring properties of the bare substrate. At the grafting density 0:12, the tilt angle of solvent particles jum ps discontinuously to a low er value. The data thus indicate that there is a rst order transition between planar and tilted anchoring.

5. D iscussion and Sum m ary

Our simulation data disclose the following scenario:We nd three di erent anchoring regimes. At low grafting densities, the anchoring on the wall is planar. At high grafting densities, it is hom eotropic, i.e., perpendicular to the wall. Tilted anchoring can be achieved in a range of interm ediate grafting densities. The transition between planar and tilted anchoring is presumably rst order. The transition between tilted and perpendicular anchoring has not been studied in detail, because simulations at high grafting densities are very expensive. The data are consistent with theoretical mean eld considerations [18], which suggest that it is continuous. A coording to theory, the anchoring behavior at high grafting densities is controlled by the structure of the interface between the polymer layer and the nem atic uid. The competition between attractive chain interactions, the translational entropy of the solvent, and its elasticity, drives a continuous transition from tilted to hom eotropic alignment.

From a practical point of view, low grafting densities are more interesting, because they can be realized more easily in experiments. The anchoring transition which we observe in that regime resembles that predicted by Halperin and W illiams [6]. However, the underlying mechanism is probably quite di erent. The theory of Halperin and W illiams relies on the existence of hairpins, abrupt reversals in the directions of the chains, whereas our \polymers" are much too short to support such defects. Nevertheless, the transition seems to be controlled by the organization of the chains in the polymer layer. We shall investigate this in more detail in a future publication [17].

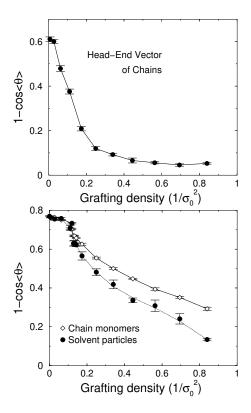


Fig. 6. A verage tilt angle h i as a function of the grafting density .Top: H ead-to-tail vector of grafted chains; B ottom : Single particles.

A cknow ledgm ents

We thank M.P.Allen for invaluable discussions.Furtherm ore, we have bene tted from useful conversations with K.Binder, D.Johannsmann, J.Ruhe, and A.Halperin.M.P.Allen and K.Binder were so kind to let us perform a major part of the simulations on the computers of their groups. This work was funded by the German Science Foundation (DFG).

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